

CLAIM AMENDMENTS

Cancel claim 1, the only claim now in this application, and substitute new claims 24 – 31 therefore. All of the claims remaining in this application after this Amendment are set forth below.

1 – 23. (cancelled)

24. (new) A re-programmable non-volatile memory formed on a substrate, comprising:

a two-dimensional array of charge storage elements extending across the substrate in first and second directions that are orthogonal with each other,

discrete source and drain regions formed in the substrate between at least some of the charge storage elements in one direction and discontinuous in the second direction,

electrical isolation between the charge storage elements and the source and drain regions in the second direction, and

electrically conductive strips elongated in the second direction and spaced apart in the first direction across and in electrical contact with the source and drain regions.

25. (new) The memory of claim 24, which additionally comprises second electrically conductive strips elongated in the first direction and spaced apart in the second direction across and field coupled with charge storage elements.

26. (new) The memory of claim 24, wherein the electrical isolation includes dielectric extending across the array in the first direction and between the charge storage elements and the source and drain regions in the second direction.

27. (new) The memory of claim 26, wherein the electrical isolation additionally includes trenches in the substrate in which the dielectric is positioned.

28. (new) The memory of claim 24, wherein the charge storage elements include conductive floating gates having a layer of dielectric between them and a surface of the substrate.

29. (new) The memory of claim 25, wherein the electrical isolation includes dielectric extending across the array in the first direction and between the charge storage elements and the source and drain regions in the second direction.

30. (new) The memory of claim 29, wherein the electrical isolation additionally includes trenches in the substrate in which the dielectric is positioned.

31. (new) The memory of claim 29, wherein the charge storage elements include conductive floating gates having a layer of dielectric between them and a surface of the substrate.